## 2SD2374, 2SD2374A

### Silicon NPN triple diffusion planar type

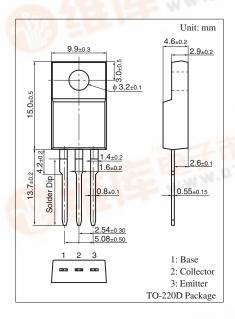
# For power amplification Complementary to 2SB1548 and 2SB1548A

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub> which has satisfactory linearity
- ullet Low collector to emitter saturation voltage  $V_{\text{CE(sat)}}$
- Full-pack package which can be installed to the heat sink with one screw

#### ■ Absolute Maximum Ratings $T_C = 25$ °C

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Parameter		Symbol	Rating	Unit		
Collector to base	2SD2374	$V_{CBO}$	60	V		
voltage	2SD2374A	and the	80			
Collector to	2SD2374	V <sub>CEO</sub>	60	V		
emitter voltage	2SD2374A	A W	80			
Emitter to base voltage		V <sub>EBO</sub>	6	V		
Peak collector current		$I_{CP}$	5	A		
Collector current		$I_{C}$	3	A		
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	25	W		
dissipation	$T_a = 25$ °C		2			
Junction temperature		T <sub>j</sub>	150	°C		
Storage temperature		$T_{stg}$	-55 to +150	°C		

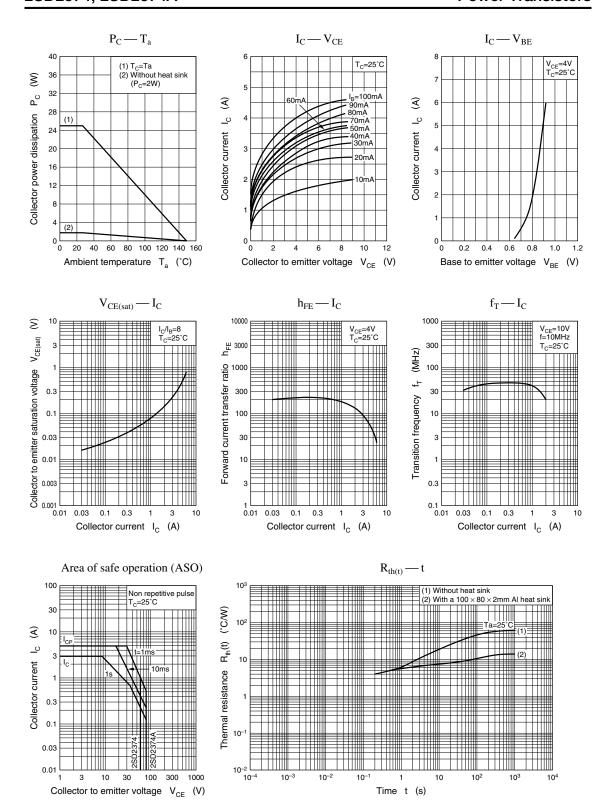


### ■ Electrical Characteristics T<sub>C</sub> = 25°C

Paramete	er	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff	2SD2374	I <sub>CES</sub>	$V_{CE} = 60 \text{ V}, V_{BE} = 0$			200	μΑ
current	2SD2374A		$V_{CE} = 80 \text{ V}, V_{BE} = 0$			200	
Emitter cutoff	2SD2374	$I_{CEO}$	$V_{CE} = 30 \text{ V}, I_{B} = 0$			300	μΑ
current	2SD2374A		$V_{CE} = 60 \text{ V}, I_{B} = 0$			300	- M
Emitter cutoff current		$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_{C} = 0$			1 🖖	mA
Collector to emitter voltage		$V_{CEO}$	$I_C = 30 \text{ mA}, I_B = 0$	60			V
Forward current transfer ratio		h <sub>FE1</sub> *	$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$	70		250	
		h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	10			
Base to emitter voltag	e	V <sub>BE</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$			1.8	V
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.375 \text{ A}$			1.2	V
Transition frequency		$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time		t <sub>on</sub>	$I_C = 1 \text{ A}, I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A},$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = 50 \text{ V}$		2.5		μs
Fall time		$t_{\mathrm{f}}$			0.4		μs

Note : Rank classification

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Rank	Q	Р				
zsc.dam	70 to 150	120 to 250				



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